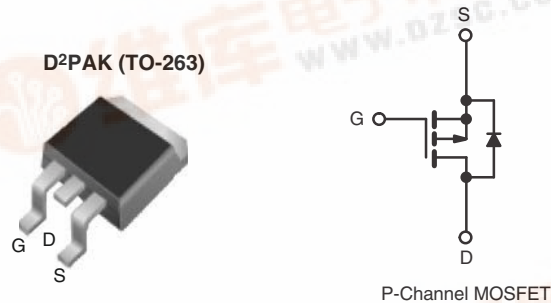


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	- 100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = - 10$ V	0.20
$Q_g$ (Max.) (nC)	61	
$Q_{gs}$ (nC)	14	
$Q_{gd}$ (nC)	29	
Configuration	Single	



### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- P-Channel
- 175 °C Operating Temperature
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
 COMPLIANT  
 HALOGEN  
**FREE**  
 Available

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK (TO-263) is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION		
Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHF9540S-GE3	SiHF9540STRL-GE3 <sup>a</sup>
Lead (Pb)-free	IRF9540SPbF	IRF9540STRLPbF <sup>a</sup>
	SiHF9540S-E3	SiHF9540STL-E3 <sup>a</sup>
SnPb	IRF9540S	IRF9540STRL <sup>a</sup>
	SiHF9540S	SiHF9540STL <sup>a</sup>

#### Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	- 100	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current	$V_{GS}$ at - 10 V	$T_C = 25$ °C	- 19	A
		$T_C = 100$ °C	- 13	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	- 72	W/°C	
Linear Derating Factor		1.0		
Linear Derating Factor (PCB Mount) <sup>e</sup>		0.025		
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	640	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$	- 19	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	15	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	150	W	
Maximum Power Dissipation (PCB Mount) <sup>e</sup>		3.7		
Peak Diode Recovery $dV/dt$ <sup>c</sup>	$dV/dt$	- 5.5	V/ns	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = - 25$  V, starting  $T_J = 25$  °C,  $L = 2.7$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = - 19$  A (see fig. 12).
- $I_{SD} \leq - 19$  A,  $dI/dt \leq 200$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material)

\* Pb containing terminations are not RoHS compliant, exemptions may apply



THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	$R_{thJA}$	-	-	40	°C/W	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	-	1.0		

**Note**

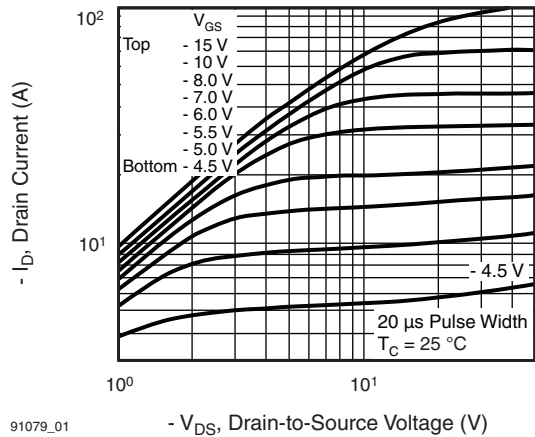
a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		- 100	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = -1\text{ mA}$		-	- 0.087	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		- 2.0	-	- 4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$		-	-	- 100	$\mu\text{A}$
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -11\text{ A}^b$	-	-	0.20	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = -50\text{ V}, I_D = -11\text{ A}$		6.2	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	1400	-	pF
Output Capacitance	$C_{oss}$			-	590	-	
Reverse Transfer Capacitance	$C_{rss}$			-	140	-	
Total Gate Charge	$Q_g$	$V_{GS} = -10\text{ V}$	$I_D = -19\text{ A}, V_{DS} = -80\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	61	nC
Gate-Source Charge	$Q_{gs}$			-	-	14	
Gate-Drain Charge	$Q_{gd}$			-	-	29	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -19\text{ A}, R_G = 9.1\text{ }\Omega, R_D = 2.4\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	16	-	ns
Rise Time	$t_r$			-	73	-	
Turn-Off Delay Time	$t_{d(off)}$			-	34	-	
Fall Time	$t_f$			-	57	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode		-	-	- 19	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	- 72	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = -19\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	- 5.0	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = -19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	130	260	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.35	0.70	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

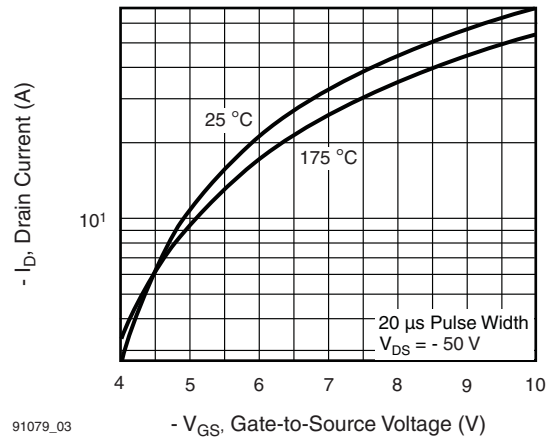
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



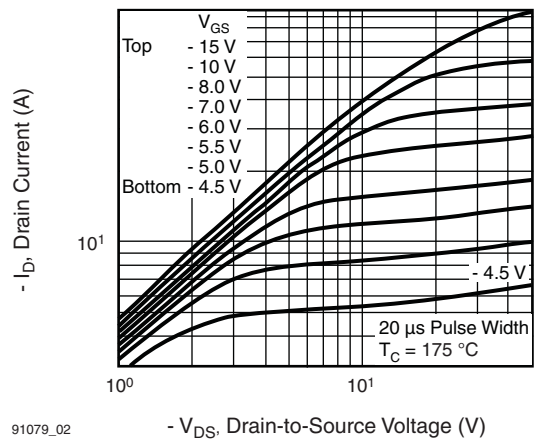
91079\_01

**Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$**



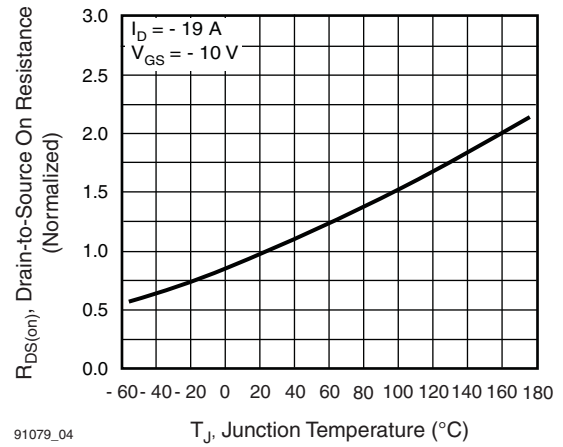
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**Fig. 3 - Typical Transfer Characteristics**



91079\_02

**Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^\circ\text{C}$**



91079\_04

**Fig. 4 - Normalized On-Resistance vs. Temperature**

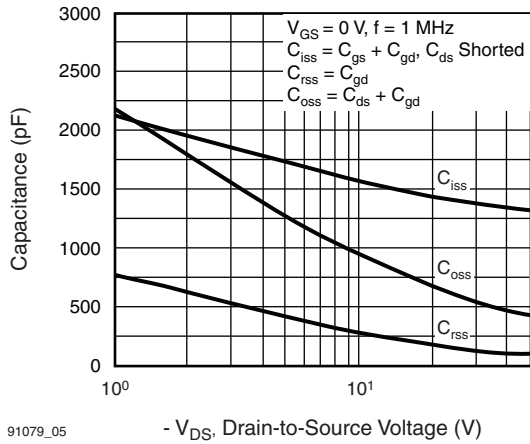


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

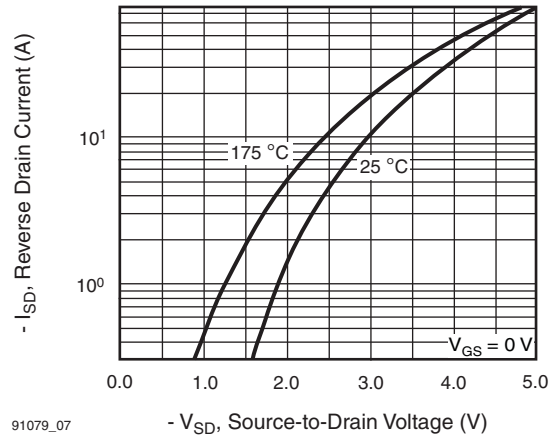


Fig. 7 - Typical Source-Drain Diode Forward Voltage

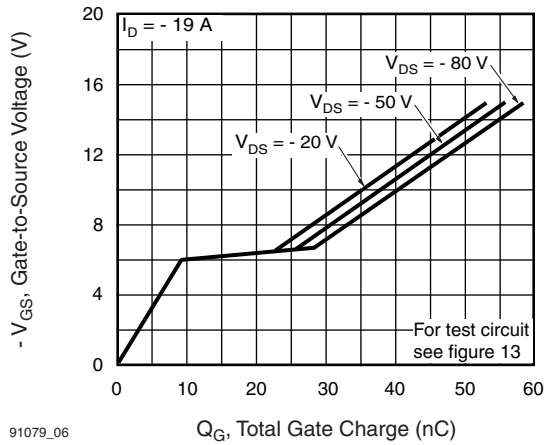


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

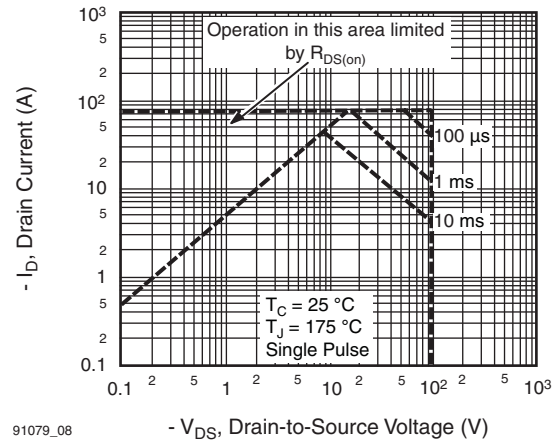
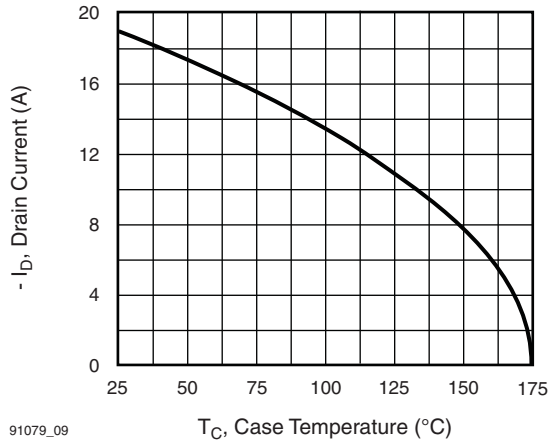
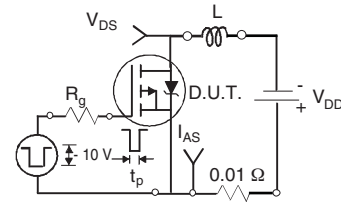


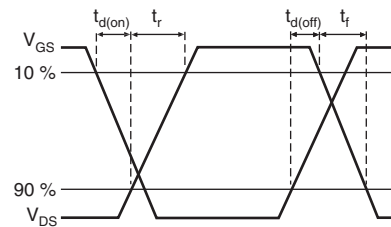
Fig. 8 - Maximum Safe Operating Area



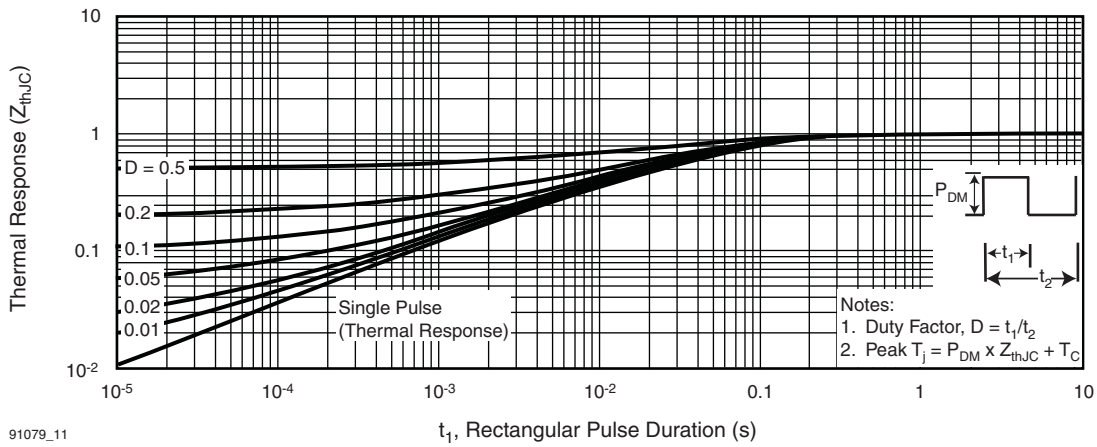
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



**Fig. 10a - Switching Time Test Circuit**



**Fig. 10b - Switching Time Waveforms**



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

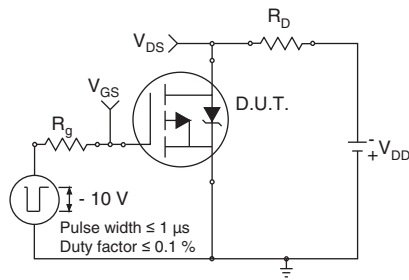


Fig. 12a - Unclamped Inductive Test Circuit

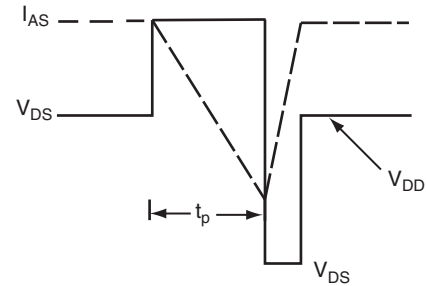


Fig. 12b - Unclamped Inductive Waveforms

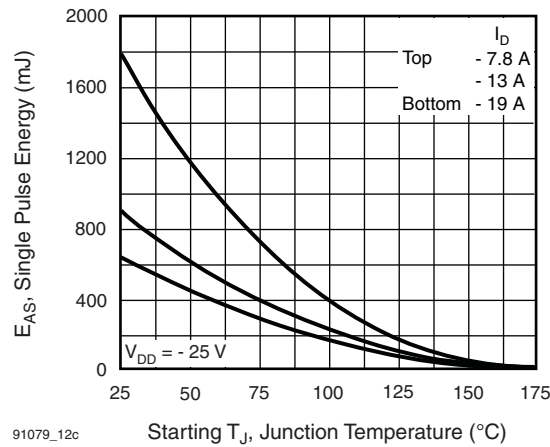


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

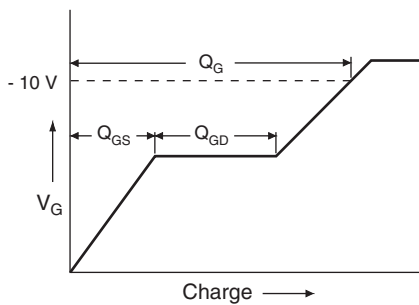


Fig. 13a - Basic Gate Charge Waveform

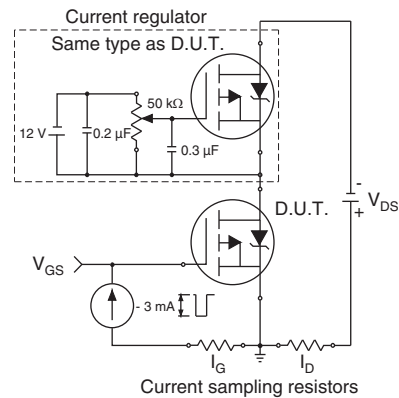
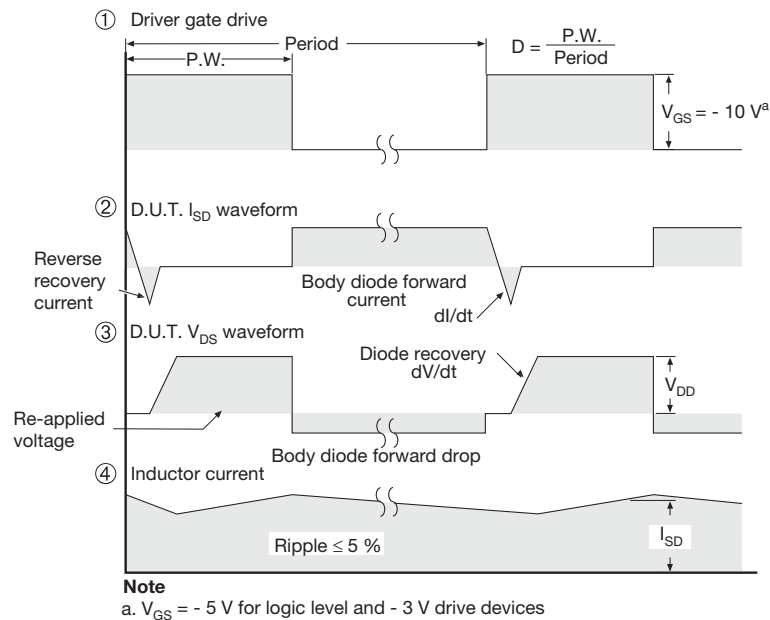
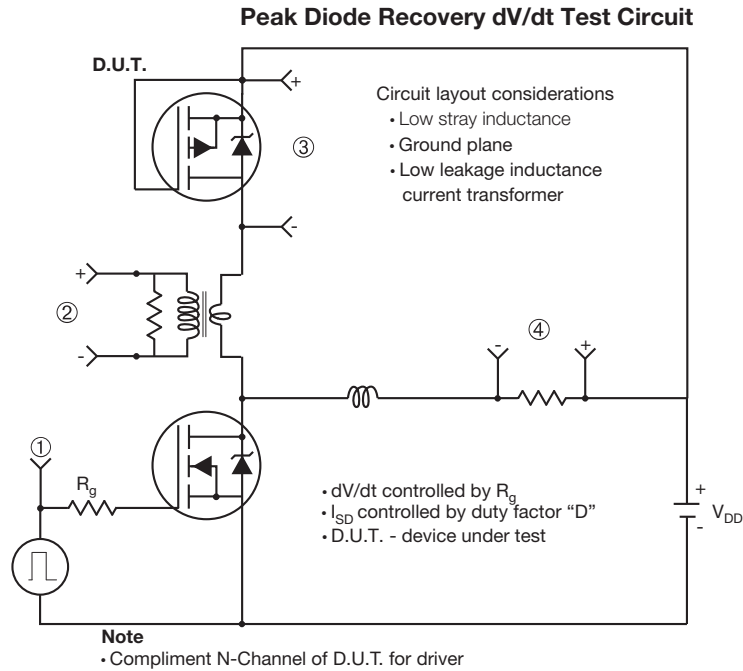


Fig. 13b - Gate Charge Test Circuit



**Fig. 14 - For P-Channel**

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